

IN THE CLAIMS

Claims 1-33 (Canceled).

34. (Currently Amended) A coated article, comprising:

a substrate, wherein the substrate is (i) metal, and comprises at least one element from the group consisting of molybdenum, tungsten, iron, nickel, aluminum, and titanium, (ii) silicon, or (iii) silica; and

a coating directly contacting and overlying the substrate, the coating having a thickness greater than about 10 microns and consisting essentially of a garnet crystal structure, wherein the substrate has a coefficient of thermal expansion at least about 30% greater than or less than a thermal expansion coefficient of the coating.

35. (Canceled)

36. (Currently Amended) The article of claim 35 34, wherein the substrate comprises an iron-based or nickel-based superalloy.

37. (Currently Amended) The article of claim 35 34, wherein the substrate comprises a stainless steel alloy.

Claims 38-42 (Canceled).

43. (Original) The article of claim 34, wherein the coating has a thickness of at least about 50 microns.

44. (Original) The article of claim 34, wherein the coating has a thickness at least about 100 microns.

45. (Previously Presented) The article of claim 34, wherein the predominant phase of the coating and the powder is said garnet crystal structure.

46. (Currently Amended) A semiconductor processing tool, comprising:  
a substrate, wherein the substrate is (i) metal, and comprises at least one element from the  
group consisting of molybdenum, tungsten, iron, nickel, aluminum, and titanium,  
(ii) silicon, or (iii) silica; and  
a coating overlying the substrate, the coating being formed by thermal spraying a ceramic  
powder comprising a garnet crystal structure, whereby the coating consists  
essentially of a garnet crystal structure phase, and the coating has a thickness  
greater than about 10 microns.

47. (Original) The tool of claim 46, wherein the processing tool is selected from the  
group consisting of a deposition apparatus, a diffusion apparatus, an etch apparatus, a chemical  
mechanical polishing apparatus, and annealing apparatus.

48. (Original) The tool of claim 47, wherein the processing tool is an etch apparatus.

49. (Original) The tool of claim 48, wherein the etch apparatus includes an etching  
chamber defined by a base upon which is disposed a lid, the etch apparatus including an  
electrostatic chuck disposed in the chamber for holding a semiconductor wafer.

50. (Original) The tool of claim 49, wherein the substrate includes at least one of the  
base, the lid, and the electrostatic chuck.

51. (Original) The tool of claim 49, wherein the etch apparatus further includes focus  
ring disposed in the chamber, positioned to surround a semiconductor wafer, and a liner, wherein  
the electrostatic chuck is disposed radially within the liner.

52. (Original) The tool of claim 51, wherein the substrate includes at least one of the ring  
and the liner.

53. (Original) The tool of claim 49, wherein the lid is in the form of a dome.

Claims 54-64 (Canceled).